



***EFFECTS OF SINTERING TEMPERATURE ON MORPHOLOGY AND
DIELECTRIC PROPERTIES OF SrTiO_3 -DOPED $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$ PREPARED
VIA MECHANICAL ALLOYING***

MUTIA SUHAIBAH BINTI ABDULLAH

ITMA 2018 22



**EFFECTS OF SINTERING TEMPERATURE ON MORPHOLOGY AND
DIELECTRIC PROPERTIES OF SrTiO_3 -DOPED $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$
PREPARED VIA MECHANICAL ALLOYING**

By

MUTIA SUHAIBAH BINTI ABDULLAH

**Thesis Submitted to the School of Graduate Studies, Universiti Putra
Malaysia, in Fulfilment of the Requirements for the Degree of Doctor
of Philosophy**

December 2018

All material contained within the thesis, including without limitation text, logos, icons, photographs and all other artwork, is copyright material of Universiti Putra Malaysia unless otherwise stated. Use may be made of any material contained within the thesis for non-commercial purposes from the copyright holder. Commercial use of material may only be made with the express, prior, written permission of Universiti Putra Malaysia.

Copyright © Universiti Putra Malaysia



Abstract of thesis presented to the Senate of Universiti Putra Malaysia in
fulfilment of the requirement for the degree of Doctor of Philosophy

**EFFECTS OF SINTERING TEMPERATURE ON MORPHOLOGY AND
DIELECTRIC PROPERTIES OF SrTiO₃-DOPED CaCu₃Ti₄O₁₂
PREPARED VIA MECHANICAL ALLOYING**

By

MUTIA SUHAIBAH BINTI ABDULLAH

December 2018

Chair : Jumiah Hassan, PhD
Faculty : Institute of Advanced Technology

Perovskite materials are well known for their ability to produce high dielectric constant which had led to many important industrial applications in microelectronics and memory devices. In this research, the relationship between morphology and dielectric properties of perovskite Strontium Titanate, ST and the perovskite-related material Calcium Copper Titanate, CCTO were studied. Most of the works done on CCTO-ST system basically cover the composition of CCTO-ST towards their electrical properties, effect of doping and their dielectric and microstructure relationship at higher sintering temperatures. However, not much work was done on tracking the evolution of CCTO-ST at low sintering temperature until they evolve to their final sintering temperature. Hence, in this thesis, research findings on the parallel evolution of such morphological properties and dielectric properties were reported and elucidate their relationship. CCTO, ST and CCTO doped with ST were prepared via mechanical alloying using High Energy Ball Milling in a hardened steel vial for 10, 12 and 2 hours respectively. The pellet samples were sintered from 500 °C to final temperature at 100 °C increment. The phase and crystal structure formation of the synthesized materials were confirmed by X-ray diffraction (XRD) while the evolution of microstructure properties was studied using Field Emission Scanning Electron Microscopy, FeSEM. The as-milled ceramic confirmed the existence of CCTO peak for the CCTO and CCTO-ST samples. After the sintering process, the highly crystalline phase of ST, CCTO and CCTO-ST was form at 1000 °C, 1000 °C and 800 °C respectively. FeSEM revealed an improvement in grain growth as the sintering increased where the grain size increased from 126.5 nm to 559.6 nm (ST), 82 nm to 18467 nm (CCTO) and from 114.54 nm to 1658.02

nm (CCTO-ST). The relative densities also show an increment where it reaches 73.59%, 98.92% and 22.26% for CCTO, ST and CCTO-ST respectively at their final sintering temperature. The dielectric studies were carried out by using Impedance Analyzer in the frequency range 40 Hz to 1 MHz and varies from 30 °C to 200 °C. For ST samples, the dielectric constant showed interfacial polarization at low frequency and ϵ_r' value increases from 49.753 to 517.603 at 100 kHz as the sintering temperature arise. Meanwhile, tangent loss ($\tan \delta$) was found in the range of 0.069 to 0.02 at 100 kHz at room temperature. For CCTO, the permittivity studies showed two polarizations occur. The relaxation belonged to the interfacial polarization. At 100 kHz, the ϵ_r' varies from 72 to 5573 for CCTO samples sintered at 500 °C to 1100 °C. The frequency dependence of loss tangent, $\tan \delta$ decreased to almost zero at higher frequencies for all sintering temperatures. The influence of ST on CCTO system does improved the microstructure and reduced the dielectric properties. The dielectric constant for CCTO-ST nanocomposite is lower than in CCTO ceramics which in the range of 139.956 at 100 kHz. However ST as a dopant also reduced $\tan \delta$ to 0.03. CCTO-ST sintered at 1000 °C showed a prominent candidate for energy storage devices as it has the lowest tangent loss and moderate ϵ_r' .

Abstrak tesis yang dikemukakan kepada Senat Universiti Putra Malaysia
sebagai memenuhi keperluan untuk ijazah Doktor Falsafah

**KESAN SUHU KE ATAS SIFAT MORFOLOGI DAN SIFAT DIELEKTRIK
SrTiO₃-DIDOPKAN KEPADA CaCu₃Ti₄O₁₂ DISEDIAKAN MELALUI
KAEDAH PENGALOIAN MEKANIKAL**

Oleh

MUTIA SUHAIBAH BINTI ABDULLAH

Disember 2018

Pengerusi : Jumiah Hassan, PhD
Fakulti : Institut Teknologi Maju

Bahan perovskite terkenal kerana keupayaannya menghasilkan pemalar dielektrik tinggi yang telah menyebabkan banyak aplikasi perindustrian penting dalam mikroelektronik dan peranti memori. Dalam kajian ini, hubungan antara morfologi dan sifat dielektrik perovskite Strontium Titanat, ST dan bahan berkaitan perovskite Kalsium Kuprum Titanat, CCTO telah dikaji. Kebanyakan kajian yang dilakukan pada sistem CCTO-ST pada dasarnya meliputi komposisi CCTO-ST terhadap sifat elektrik mereka, kesan doping dan hubungan dielektrik dan mikrostruktur mereka pada suhu sintering yang lebih tinggi. Walau bagaimanapun, tidak banyak penyelidikan yang dilakukan untuk mengesan evolusi CCTO-ST pada suhu sintering yang rendah sehingga mereka berubah menjadi suhu sintering terakhir mereka. Oleh itu, dalam tesis ini, beberapa penemuan penyelidikan mengenai evolusi selari sifat morfologi dan sifat dielektrik tersebut dilaporkan dan menjelaskan hubungan mereka. Seramik ST, CCTO dan CCTO didopkan ST telah disediakan melalui kaedah pengaloiian mekanikal menggunakan pengisaran bebola bertenaga tinggi di dalam botol keluli keras selama beberapa jam. Bagi mendapatkan siri suhu yang berubah, sampel disinterkan dari suhu 500 ke 1400 °C pada peningkatan 100 °C. Pembentukan struktur fasa dan kristal bahan-bahan yang disintesis telah disahkan oleh analisis pembelauan sinar-X (XRD) manakala evolusi sifat-sifat mikro telah dikaji menggunakan Mikroskopi Pengimbasan Elektron Pelepasan Medan, FeSEM. Seramik sesudah pengisaran mengesahkan adanya puncak CCTO untuk sampel CCTO dan CCTO-ST. Selepas proses pemanasan, fasa ST, CCTO dan CCTO-ST yang sangat kristal dibentuk pada 1000 °C, 1000 °C dan 800 °C. Pemerhatian oleh FeSEM menunjukkan peningkatan dalam pertumbuhan bijirin apabila sintering meningkat di mana saiz butiran meningkat dari 126.5 nm ke 559.6 nm (ST), 82 nm ke 18467 nm (CCTO) dan dari 114.54 nm ke

1658.02 nm. Ketumpatan relatif juga menunjukkan kenaikan di mana ia mencapai 73.59%, 98.92% dan 22.26% untuk CCTO, ST dan CCTO-ST masing-masing pada suhu sintering terakhir mereka. Kajian dielektrik dilakukan dengan menggunakan Impedance Analyzer dalam julat frekuensi 40 Hz hingga 1 MHz dan berbeza dari 30 °C hingga 200 °C. Bagi sampel ST, pemalar dielektrik menunjukkan polarisasi interfacial pada frekuensi rendah dan nilai ϵ_r meningkat daripada 49.753 ke 517.603 pada 100 kHz apabila suhu sintering meningkat. Sementara itu, kehilangan tangent didapati dalam julat 0.069 hingga 0.02 pada 100 kHz pada suhu bilik. Bagi CCTO, kajian ketelusan menunjukkan dua polarisasi berlaku. Kelonggaran itu tergolong dalam polarisasi antara muka. Pada 100 kHz, ϵ_r berbeza dari 72 hingga 5573 untuk sampel CCTO yang disinter pada 500 °C hingga 1100 °C. Ketergantungan frekuensi kehilangan tangent, $\tan \delta$ menurun kepada hampir nol pada frekuensi yang lebih tinggi untuk semua suhu sintering. Pengaruh sistem ST pada sistem CCTO memperbaiki struktur mikro dan mengurangkan sifat dielektrik. Pemalar dielektrik untuk nanocomposite CCTO-ST adalah lebih rendah daripada seramik CCTO iaitu 139.956 pada 100 kHz. Bagaimanapun ST sebagai dopan juga berkurangan $\tan \delta$ kepada 0.03. CCTO-ST sintered pada 1000 °C menunjukkan calon yang terkenal untuk peranti storan tenaga kerana ia mempunyai kehilangan tangent terendah dan sederhana ϵ_r .

ACKNOWLEDGEMENTS

Alhamdulillah, I praise and thank Allah for giving me the strength and patience to work through all these years.

To my supervisor, Associate Professor Dr Jumiah Hassan, thank you for introducing me to the field and for outlining this research, your help and guidance along the way. I also appreciate the control you gave me over this research and the freedom I had to pursue my own ideas.

I am deeply indebted my co-supervisor (late), Associate Professor Dr Mansor Hashim for his expert guidance and keen interest throughout the course of this study. Unfortunately, before completion of the thesis, he left us forever. I cherish his dedication in guiding me in my work despite of his ill health. I wish his soul rest in peace and solace in the heaven.

I would like to deeply thank the people who mean world to me, my parents, Hj Abdullah bin Daud and Hjh Fatilah Hasni Ab Latif. I cannot begin to say how much I appreciate their support and love. I would never be able to pay back the love and affection showered upon by my parents. I am especially grateful to my siblings for their endless patience and supporting me spiritually throughout my life.

I owe thanks to a very special person, my husband, Muhammad Aizat Noor Ismail for his continued support and understanding during my pursuit of Ph.D that made the completion of thesis possible. You were always around at times I thought that it is impossible to continue, you helped me to keep things in perspective.

Most importantly of all, I show extensive gratitude to my very best lab mates, Dayang Nur Fazliana Abdul Halim for always being there and bearing with me the good and bad times during my wonderful days of Ph.D. Without her willingness to share, the research would not have even been possible.

There are many more who deserve my gratitude, far too many to list here. Collective thanks to the Institute of Advanced Technology and Department of Physics, UPM for providing me with the requisite institutional facilities throughout my research tenure. I am equally thankful to Mrs. Sarinawani and Mr. Ali for their assistance with FeSEM measurements, Mr. Mohd Kadri Masaud and Dr. Ismayadi bin Ismail for the great contributions and helps, Mr. Mohd Anas Ahmad from USM and Mr. Nizam from UKM for making the facilities available during the research work.

My heartfelt thanks to my fellow labmates, Dr. Shamsul Ezzad, Dr. Rodziah Nazlan, Dr. Nor Hapishah Abdullah, Dr. Wan Norailiana Wan Ab Rahman, Dr. Fadzidah Mohd Idris, Dr. Idza Riati Ibrahim, Dr. Muhammad Syazwan Mustaffa, Dr. Alex See, Mr. Muhammad Misbah Muhamad Zulkimi, Mr. Ikhwan and Mr. Che Sulaiman Ahmad, who helped me by creating a stimulating and exciting working atmosphere, by sharing their views and advice and by organising and participating in all the events. There were many fun times, sometimes needed to take my mind off the research or get perspective on things. I will always remember and cherish those times.

I take this opportunity to sincerely acknowledge Ministry of Higher Education Malaysia for providing financial assistance through myBrain15 scholarship which supported me to pursue my research conveniently.

This thesis was submitted to the Senate of Universiti Putra Malaysia and has been accepted as fulfilment of the requirement for the degree of Doctor of Philosophy. The members of the Supervisory Committee were as follows:

Jumiah Hassan, PhD

Associate Professor
Faculty of Science
Universiti Putra Malaysia
(Chairman)

Mansor Hashim, PhD

Associate Professor
Institute of Advanced Technology
Universiti Putra Malaysia
(Member)

Suriati Paiman, PhD

Associate Professor
Faculty of Science,
Universiti Putra Malaysia
(Member)

Rosli Hussin, PhD

Professor
Faculty of Science,
Universiti Teknologi Malaysia
(Member)

ROBIAH BINTI YUNUS, PhD

Professor and Dean
School of Graduate Studies
Universiti Putra Malaysia

Date:

Declaration by graduate student

I hereby confirm that:

- this thesis is my original work;
- quotations, illustrations and citations have been duly referenced;
- this thesis has not been submitted previously or concurrently for any other degree at any other institutions;
- intellectual property from the thesis and copyright of thesis are fully-owned by Universiti Putra Malaysia, as according to the Universiti Putra Malaysia (Research) Rules 2012;
- written permission must be obtained from supervisor and the office of Deputy Vice-Chancellor (Research and Innovation) before thesis is published (in the form of written, printed or in electronic form) including books, journals, modules, proceedings, popular writings, seminar papers, manuscripts, posters, reports, lecture notes, learning modules or any other materials as stated in the Universiti Putra Malaysia (Research) Rules 2012;
- there is no plagiarism or data falsification/fabrication in the thesis, and scholarly integrity is upheld as according to the Universiti Putra Malaysia (Graduate Studies) Rules 2003 (Revision 2012-2013) and the Universiti Putra Malaysia (Research) Rules 2012. The thesis has undergone plagiarism detection software.

Signature: _____ Date: _____

Name and Matric No.: Mutia Suhaibah binti Abdullah (GS31552)

Declaration by Members of Supervisory Committee

This is to confirm that:

- the research conducted and the writing of this thesis was under our supervision;
- supervision responsibilities as stated in the Universiti Putra Malaysia (Graduate Studies) Rules 2003 (Revision 2012-2013) are adhered to.

Signature: _____
Name of Chairman
of Supervisory Committee: Jumiah Hassan

Signature: _____
Name of Member of
Supervisory Committee: Mansor Hashim

Signature: _____
Name of Member of
Supervisory Committee: Suriati Paiman

Signature: _____
Name of Member of
Supervisory Committee: Rosli Hussin

TABLE OF CONTENTS

	Page
ABSTRACT	i
ABSTRAK	iii
ACKNOWLEDGEMENTS	v
APPROVAL	vii
DECLARATION	ix
LIST OF TABLES	xiv
LIST OF FIGURES	xv
LIST OF ABBREVIATIONS	xix
 CHAPTER	
 1 INTRODUCTION	
1.1 Background of the study	1
1.2 Dielectric Materials	1
1.3 Problem Statement	3
1.4 Objectives	4
1.4.1 Main Research-Project Objective	4
1.4.2 Work-step Objectives	4
1.5 Limitations of the study	4
1.6 Thesis outline	4
 2 LITERATURE REVIEW	
2.1 Introduction	6
2.2 Mechanical Alloying	6
2.2.1 Historical perspective of Mechanical Alloying	6
2.2.2 Mechanical Alloying for Dielectric Materials	7
2.2.3 Process Variables	8
2.2.3.1 Type of mills	8
2.2.3.2 Milling Container	10
2.2.3.3 Milling Speed	10
2.2.3.4 Milling Time	11
2.2.3.5 Ball to powder weight ratio	11
2.3 Relationship of microstructure with Dielectric properties	12
2.3.1 Grain size effects on dielectric properties	13
2.3.2 Porosity effects on dielectric properties	14
2.3.3 Sintering Temperature effects on dielectric properties	15
2.4 Material selection	15
2.4.1 $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$ (CCTO)	15
2.4.2 SrTiO_3 (ST)	17
2.4.3 Doped CCTO	18

3 THEORY

3.1	Overview	19
3.2	CaCu ₃ Ti ₄ O ₁₂ : Background and structural properties	19
3.3	SrTiO ₃ : Background and structural properties	19
3.4	Dielectric Response Parameter	21
3.4.1	Dielectric constant	21
3.4.2	Dielectric Loss	23
3.5	Polarization Mechanism	24
3.6	Impedance Spectroscopic Studies	26
3.7	Factors affecting dielectric properties	29
3.8	Doping effect	30

4 METHODOLOGY

4.1	Introduction	31
4.2	Research design	31
4.3	Raw Materials	31
4.4	Preparation of nanoparticles	32
4.4.1	Preparation of CCTO	32
4.4.2	Preparation of ST	32
4.4.3	Preparation of CCTO doped with ST	34
4.5	Binder	36
4.6	Lubricant	36
4.7	High Energy Ball Milling	37
4.8	Granulation	38
4.9	Moulding	38
4.10	Sintering	38
4.11	Material Characterization Techniques and Studied Parameter	39
4.11.1	Physical Characterization	39
4.11.1.1	Transmission Electron Microscope (TEM)	39
4.11.1.2	X-Ray Diffraction (XRD)	41
4.11.1.3	Field Emission Scanning Electron Microscope (FESEM)	43
4.11.1.4	Density	43
4.11.1.5	Porosity	44
4.11.2	Dielectric Characterization	45
4.12	Error Estimation	46

5 RESULTS AND DISCUSSION

5.1	Introduction	47
5.2	Calcium Copper Titanate (CCTO)	47

5.2.1	Particle size analysis	47
5.2.2	Phase analysis	47
5.2.3	Density	51
5.2.4	Microstructure	52
5.2.5	Dielectric properties of CCTO	56
5.2.6	Impedance and Electric modulus Study	64
5.3	Strontium Titanate (SrTiO_3)	68
5.3.1	Particle size analysis	68
5.3.2	Phase analysis	68
5.3.3	Density	71
5.3.4	Microstructure	72
5.3.5	Dielectric properties of ST	77
5.3.6	Impedance and Electric Modulus Study	85
5.4	CCTO doped with SrTiO_3	90
5.4.1	Particle size analysis	90
5.4.2	Phase analysis	90
5.4.3	Density	94
5.4.4	Microstructure	95
5.4.5	Dielectric properties of CCTO-ST	97
5.4.6	Impedance and Electric Modulus Study	104
5.5	Influence of SrTiO_3 on CCTO	108
5.5.1	Phase analysis	108
5.5.2	Microstructure	108
5.5.3	Dielectric properties	110
5.5.4	Impedance Study	111
6	CONCLUSION AND RECOMMENDATIONS FOR FUTURE RESEARCH	
6.1	Conclusions	113
6.2	Recommendations For Future Research	114
	REFERENCES	115
	APPENDIX	121
	BIODATA OF STUDENT	124
	LIST OF PUBLICATIONS	125

LIST OF TABLES

Table		Page
2.1	Physical properties of SrTiO_3 sample at various milling times after sintering at 1200 °C	11
3.1	Physical properties of SrTiO_3	20
4.1	Raw materials used for the synthesis of nanoparticles	31
4.2	Parameters for ball-milling of CCTO	32
4.3	Parameters for ball-milling of ST	34
4.4	Parameters for ball-milling of CCTO-ST	35
4.5	Physical properties of polyvinyl alcohol	36
4.6	Properties of Zinc Stearate	37
4.7	Error estimation for measuring equipment	46
5.1	Properties of the CCTO samples with different sintering temperatures	53
5.2	Dielectric constant and loss tangent of CCTO at different sintering temperatures measured at room temperature.	60
5.3	Physical properties of SrTiO_3 ceramics at different sintering temperatures	74
5.4	Dielectric constant and loss tangent of ST at different sintering temperatures measured at room temperature.	81
5.5	Main performance parameters of SrTiO_3 -doped CCTO ceramics	93
5.6	Atomic percentage of elements for CCTO-ST sintered at different sintering temperatures	97
5.7	Dielectric constant and loss tangent of CCTO-ST at different sintering temperatures	101
5.8	Properties of CCTO and CCTO-ST sintered at 1000 °C	110

LIST OF FIGURES

Figure		Page
2.1	Effect of milling time on grain size of Cr	9
2.2	Temperature dependence of the dielectric constant in various grain-size high-purity BaTiO ₃ ceramics	14
2.3	Sintering temperature dependence of the dielectric constant and loss tangent at 10 kHz for samples sintered for 10 h at room temperature	15
3.1	CaCu ₃ Ti ₄ O ₁₂ structure drawn with TiO ₆ octahedra, Cu as black spheres, O as white spheres, and Ca at the origin and cubic center	20
3.2	(a) SrTiO ₃ unit cell of structure, (b) SrTiO ₃ polymorph distortion of the perovskite structure and (c) Phase diagram of the system SrO-TiO ₂	22
3.3	Loss tangent and derivation of dissipation factor	24
3.4	Schematic of (a) electronic polarization, (b) ionic polarization, (c) orientational polarization, (d) space charge polarization.	24
3.5	General view of the polarization mechanisms as a function of frequency showing approximate mechanism as to where polarization takes place	25
3.6	Nyquist plot and its equivalent circuit representation	27
4.1	Flowchart for the preparation and characterization of the CCTO	33
4.2	Flowchart for the preparation and characterization of the ST	34
4.3	Flowchart for the preparation and characterization of the CCTO-ST	35
4.4	Polyvinyl Alcohol (PVA)	36
4.5	(a) SPEX Dual Mixer/Mill 8000D, (b) hardened steel vial and grinding media	37
4.6	Sintering Profile	39
4.7	a) LEO 912AB Energy Filter TEM b) TEM copper grid covered with a lacey carbon film	40
4.8	a) General layout of a TEM describing the path of electron beam in a TEM b) A ray diagram for the diffraction mechanism in TEM	40
4.9	Common configurations for an XRD unit	41
4.10	Principle of X-ray Diffraction	42

4.11	A schematic diffractogram showing the presence of two phases (with peaks at different angular positions) originating from a material with small and large crystallites. The broad hump is due to an amorphous phase	42
4.12	Principle of Scanning Electron Microscope	44
4.13	Schematic diagram of dielectric measurement set-up	46
5.1	Transmission electron microscopy image of as-milled raw powder	48
5.2	Starting particle size distribution after 10 hours of milling.	48
5.3	XRD pattern of CCTO samples at different sintering temperatures compared with the diffraction peaks of the starting materials.	50
5.4	CCTO lattice parameter, a vs sintering temperature determined from XRD.	51
5.5	Experimental and theoretical density of $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$ for different sintering temperatures.	51
5.6	FESEM images on the surface of CCTO pellets sintered at different temperature for 10 hours	54
5.7	Temperature dependence of grain size of the CCTO samples	56
5.8	Temperature -dependence of dielectric constant and $\tan \delta$ of CCTO with a) 500 °C, b) 600 °C, c) 700 °C, d)800 °C, e) 900 °C f) 1000 °C and g) 1100 °C sintering temperatures at various frequencies	58
5.9	Frequency dependence of dielectric constant and loss tangent of CCTO with (a) 500 °C, (b) 600 °C, (c) 700 °C ,(d) 800 °C,(e) 900 °C, (f) 1000 °C, and (g) 1100 °C sintering temperatures	60
5.10	Frequency-dependence of dielectric constant and $\tan \delta$ at different sintering temperatures at a) 30 °C, b) 50 °C, c) 80 °C, d) 110 °C, e) 140 °C f) 170 °C and g) 200 °C	62
5.11	Frequency-dependence of Z'' and M'' at different sintering temperatures at a) 30 °C, b) 50 °C, c) 80 °C, d) 110 °C, e) 140 °C f) 170 °C and g) 200 °C	65
5.12	Complex impedance plot of CCTO system at selected sintering temperatures	67
5.13	TEM micrograph of as-milled powder after 12 h of milling	68

5.14	XRD patterns of SrTiO ₃ samples showing the structural evolution as a function of the sintering temperatures	70
5.15	ST lattice parameter, a vs sintering temperature determined from XRD.	71
5.16	Variation of density and porosity as a function of sintering temperature	72
5.17	FeSEM images on the surface and grain size distributions of ST pellets sintered at 500 °C- 1400 °C for 12 hours	75
5.18	Average grain size evolution for samples sintered from 500 °C to 1300 °C	77
5.19	Frequency dependence of dielectric constant and $\tan \delta$ of ST at different sintering temperatures at a) 30 °C, b) 50 °C, c) 80 °C, d) 110 °C, e) 140 °C f) 170 °C and g) 200 °C	78
5.20	Dielectric constant as a function of (a) sintering temperature (b) grain size for SrTiO ₃ at 1 MHz	81
5.21	Frequency-dependence of Z'' and M'' of ST at different sintering temperatures at a) 30 °C, b) 50 °C, c) 80 °C, d) 110 °C, e) 140 °C f) 170 °C and g) 200 °C	82
5.22	Complex impedance plot of ST system at selected sintering temperatures	86
5.23	Transmission electron microscopy images and X-ray diffraction patterns of as-milled CCTO-ST powder	89
5.24	XRD of as-milled samples of CCTO and CCTO-ST compared with the diffraction peaks of the starting materials	90
5.25	X-ray diffraction patterns of the resultant products after sintering at temperatures from 500 to 1000 °C	92
5.26	XRD patterns of undoped CCTO and CCTO/ST ceramics sintered at 1000°C.	94
5.27	D-Spacing (Å) as a function of sintering temperature for doped CCTO.	94
5.28	SEM images of CCTO-ST ceramics sintered at different sintering temperatures	96
5.29	Average grain size vs sintering temperatures for CCTO-ST	97
5.30	Frequency dependence of dielectric constant and $\tan \delta$ of the CCTO-ST sample with different sintering	99

	temperatures and measured at various measuring temperatures	
5.31	Evolution of grain size and dielectric constant	101
5.32	Frequency dependence of dielectric constant and $\tan \delta$ of undoped CCTO and ST doped CCTO samples sintered at 1000 °C and measured at room temperature.	102
5.33	Frequency dependence of Z'' and M'' of the CCTO-ST sample with different sintering temperatures and measured at various measuring temperatures	105
5.34	Complex impedance plot of CCTO-ST system at selected sintering temperatures	107
5.35	XRD of as-milled samples of CCTO and CCTO-ST compared with the diffraction peaks of the starting materials	109
5.36	XRD patterns of undoped CCTO and CCTO/ST ceramics sintered at 1000 °C	109
5.37	FeSEM images of CCTO (a) and CCTO-ST(b) ceramics sintered at 1000 °C	110
5.38	Frequency dependence of dielectric constant and $\tan \delta$ of undoped CCTO and ST doped CCTO samples sintered at 1000 °C and measured at room temperature	111
5.39	The Cole–Cole plot of impedance at room temperature for CCTO and SrTiO_3 -doped CCTO ceramic samples sintered at 1000 °C	112

LIST OF ABBREVIATIONS

UPM	Universiti Putra Malaysia
SrTiO_3 , ST	Strontium titanate
$\text{CaCu}_3\text{Ti}_4\text{O}_{12}$, CCTO	Calcium Copper Titanate
ϵ''	Dielectric constant
$\tan \delta$	Loss Tangent
Hz	Hertz
BPR	Ball to powder weight ratio
CCTO-ST	Strontium Titanate-doped Calcium Copper Titanate
vol.	Volume
wt.	Weight
Z	Impedance
M	Electric Modulus
Y	Admittance
PVA	Poliviny Alcohol
E_a	Activation Energy
Ω	Ohm
DC	Direct current
TEM	Transmission Electron Microscopy
XRD	X-ray Diffraction
FESEM	Field Emission Electron Microscopy
EDX	Energy Dispersive X-ray Spectroscopy
ρ	Density
ρ_{xrd}	X-ray density
P_{exp}	Experimental density



CHAPTER 1

INTRODUCTION

1.1 Background of the study

On 7 March 2014, marketsandmarkets.com published a report titled "Dielectric Material Market by Technology (OLED, LED, TFT-LCD, LED-LCD, Plasma, LCOS, DLP), Application (Conventional, 3D, Transparent, Flexible), Material (Metal Oxide, a-Silicon, LTPS, PET, PEN, Photonic Crystals) & by Geography - Global Forecast to 2013 - 2020". Analysis of the report shows that the total dielectric materials market is projected to reach market revenue worth \$50.63 billion by 2020 (marketsandmarkets.com, 2014). According to this analysis, it can be concluded that the role of dielectric display materials in display panels has evolved so as to meet the changing requirements of the new and more advanced chip designs and packaging technologies. Dielectric materials are an integral part of the display panels that define the nature and the role of the displays. A lot of research directed at improving materials properties was done over the years. The progress in this field is very rapid.

Owing to the need of modern electronic industry, the synthesis methods are used to control the morphology and grain size of material. Among these methods, mechanical alloying (MA) is one of the methods that are often used to synthesize materials and can effectively control the morphology and grain size of products (Suryanarayana & Froes, 1992) MA is a solid-state powder processing technique involving repeated welding, fracturing, and rewelding of powder particles in a high-energy ball mill (Suryanarayana, 2001). It is also an economical process with important technical advantages. The usefulness of this method was well documented in literature and excellent reviews and monographs are available dealing with the different aspects. It is well established that the properties and behaviour of every material is dependent on its microstructure, and that microstructure can be controlled by the way in which the material is made and processed. Properties of dielectric materials are affected by their microstructures, especially grain size, porosity and density, which in turn, are strongly influenced by sintering temperature. With increasing sintering temperature, grain size and porosity will exhibit different development trends, which strongly influence their dielectric properties. Thus, it is important to correlate the microstructure and dielectric properties of materials relating them from nanometre grain-size microstructure until they have evolved to their final forms at their last evolution stage.

1.2 Dielectric Materials

Dielectric materials play a key role in our global society with a wide range of applications, from terrestrial and satellite communication including software, radio, GPS, and DBS TV to environmental monitoring via satellite. The last decade witnessed a well-paced transformation in the display technology market and is expected to grow further. Products such as smartphones, laptops, tablets, and TVs are garnering a very high demand from the consumers' perspective; this demand directly impacts the ever-increasing demand for the materials associated with these products.

A material is classified as "dielectric" if it has the ability to store energy when an external electric field is applied. There were no studies about the properties of insulating materials until 1837. Throughout most of the 19th century, scientists searching for insulating materials for specific applications have become increasingly concerned with the detailed physical mechanism governing the behavior of these materials. After more than eighty years of development, the theory of dielectrics is still an active area for research. Understanding the behaviour of dielectric materials with the variations of field, temperature and frequency is of particular importance for present day electronics.

In recent years, a lot of researches and attempts were conducted to find ingenious and readily available dielectric materials that could yield predictable and controllable permittivity with very low dielectric loss factor has always proved to be positive and successful. As for that, much attention was paid to $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$ (CCTO) (Homes et al., 2001; Subramanian et al., 2000; Ramirez et al., 2000), which exhibits a high dielectric constant with good temperature stability. The dielectric properties of CCTO were first reported by Subramanian et al. in 2000. They first reported that large dielectric constants were found in $\text{ACu}_3\text{Ti}_4\text{O}_{12}$ (A= trivalent rare earth or Bi) type material. CCTO, displaying the most special behavior, shows a dielectric constant of about 12,000 at 1 kHz, remaining steady in a large temperature range, from 100 K to 400 K. As we know, some materials with dielectric constants higher than 1,000 are associated with ferroelectric properties and the dielectric constant changes greatly during the ferroelectric phase transition. This property limits their applications in industry because, often it is required that the dielectric constant of the material is fairly independent of temperature. Therefore, CCTO with its low dependence on temperature is of great interest to us.

Even though CCTO has a large permittivity, its relatively high dielectric loss is one of the main problems regarding the use of CCTO in practical applications. In particular, an enhancement of ϵ is usually accompanied by an increase in dielectric loss. It is essential to decrease the dielectric loss if CCTO ceramics are to be introduced into commercial applications. Some

research results showed that the dielectric loss in CCTO ceramics mainly originates from semiconducting grains and insulating grain boundaries. Numerous attempts were made to reduce the current leakage by modifying the semiconducting properties and interfacial structure of CCTO ceramics. One effective approach is to combine the high-dielectric constant materials with another insulating oxide with low tangent loss to improve the final materials characteristics.

Perovskite-type oxides are some of the materials with high dielectric constant. The ability of the simple perovskite structure (ABO_3) to give rise to intergrowth structures, oxygen deficient structures and ordered perovskite structures are well known (Rao and Thomas, 1985; Anderson and Poeppelmeier, 1991; Anderson et al., 1993). Among the wider family of perovskite-type oxides, SrTiO_3 (ST) is a representative member of this family; it displays a cubic structure. ST is a ceramic material with high dielectric constant (ϵ_r'), low dielectric loss (ϵ_r''), large polarization and good insulating properties is a potential candidate in the electronic industry. ST has a low dielectric loss as an incipient ferroelectric, though it does not possess attractive properties in pure form. Therefore, it would be interesting to add a small amount of ST to CCTO and investigate the dielectric and electrical properties of such composite materials. Thus, it is important to correlate the microstructure and dielectric properties of CCTO, ST and CCTO-ST relating them from nanometre grain-size microstructure until they have evolved to their final forms at their last evolution stage.

1.3 Problem Statement

Most of the works carried out on CCTO-ST system basically cover the composition of CCTO-ST towards their electrical properties, effect of doping and their dielectric and microstructure relationship at higher sintering temperatures. To the best of our knowledge, reports on microstructure-property evolution study of CCTO-ST which endeavour to correlate the evolving microstructure with the dielectric properties have not been given in details. In order to obtain greater clarification on this aspect; an attempt is made in this work to synthesize CCTO-ST powders by mechanical alloying method which is followed by compacted-sample sintering in a series of ascending temperatures. Thus this research embarks on the following questions:

- What would be the dielectric-microstructure relationships at various intermediate sintering conditions during the parallel evolutions of the morphology and dielectric properties?
- Do the changes of microstructure affect the dielectric properties of the materials?
- How do dielectric properties evolve with the microstructure changes?

1.4 Objectives

1.4.1 Main Research-Project Objective

The main goal of this research is to critically track the evolution of the dielectric properties parallel to the microstructural changes starting from unusually low sintering temperature up to its final form. Previous literature has shown little evidence of synthesis work via high energy ball milling to reach nanometer grain-size region and critically track the microstructural grain growth to micron size. Thus, due to the significant amount of materials required, mechanical alloying seems to be the only practical technique in studies involving the evolution of the microstructure of the material.

1.4.2 Work-step Objectives

The work steps of the project are to ensure the successful attainment of the project objective. These are:

- i) To synthesize CCTO, ST and ST doped CCTO via mechanical alloying
- ii) To study the effect of sintering temperature on the evolving microstructural changes.
- iii) To study the dielectric behaviour of the samples
- iv) To study the dopant effect on microstructure-dielectric properties

1.5 Limitations of the study

Although the objectives and scopes in this thesis had been thoroughly investigated and studied, there are few limitations regarding to the research:

- i. The Dielectric measurement was carried out in the 40 Hz - 1MHz due to the limitation in experimental equipment constrained.

1.6 Thesis Outline

This thesis comprises of 6 chapters. In the first chapter, general introduction of evolution and materials study, microstructural-dielectric properties and some research questions are discussed. The second chapter deals with literatures of the synthesis methods, mechanical alloying and important materials properties, dielectric theory and materials properties, some microstructural consideration on dielectric properties and some overview about materials evolution studies. The third chapter presents the basic theories on titanates and sintered materials. In some aspects of the theory,

the chapter describes the basic crystal structure that controls the behavior of the dielectric materials. Experimental and measurement techniques which include sample preparation and the apparatus used for both microstructural-dielectric analyses were discussed in the fourth chapter. The fifth chapter presents the results of microstructural-dielectric analysis. The ceramics were analysed using XRD, SEM, EDX, and TEM, leading to the understanding of the microstructure evolution observed. Data obtained from dielectric measurements were also discussed. The sixth or final chapter summarizes and concludes the research findings and comments on the system in relation to microstructural-dielectric properties. Recommendations for further work are also given. The author's biography, appendices and references/bibliographies are in the last part of the thesis.



REFERENCES

- Adams, T.B., Sinclair, D.C. and West, A.R. (2002). Giant Barrier Layer Capacitance Effects in $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$ Ceramics. *Advanced Materials* 14: 1321.
- Alford, M.N. and Penn, S.J. (1996). Sintered Alumina With Low Dielectric Loss. *Journal of Applied Physics*, 80: 5895-5898.
- Almeida, A.F.L., Fechine, P.B.A., Graca, M.P.F., Valente, M.A., Sombra, A.S.B. (2009). Structural and electrical study of $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$ (CCTO) obtained in a new ceramic procedure. *Journal of Materials Science Materials in Electronics*, 20(2):163-170.
- Almeida, A.F.L., Oliviera, R.S.D., Goes, J.C., Sasaki, J.M., Filho, A.G.S., Filho, J.M. and Sombra, A.S.B. (2002). Structural properties of $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$ obtained by mechanical alloying. *Materials Science and Engineering B*, 96: 275–283.
- Anderson, M.T. and Poeppelmeier, K.R. (1991). Lanthanum copper tin oxide ($\text{La}_2\text{CuSnO}_6$): a new perovskite-related compound with an unusual arrangement of B cations. *Chemistry of Materials*, 3(3): 476-482.
- Anderson, M.T., Greenwood, K.B., Taylor, G.A. and Poeppelmeier, K.R. (1993). B-cation arrangements in double perovskites. *Progress in. Solid State Chemistry*, 22(3):197-233.
- Aoyagi, R., Iwata, M. and Maeda, M. (2007). Effect of Sintering Temperature on the Dielectric Properties of $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$ Ceramics. *Ferroelectrics* 356:90–94,
- Arlt, G., Hennings, D. and With, G.D. (1985). Dielectric properties of fine-grained barium titanate ceramics. *Journal of Applied Physics* 58: 1619
- Barsoukov, E. and Macdonald, J.R. (2005). *Impedance spectroscopy: theory, experiment, and applications*. John Wiley and Sons.
- Buessen, W.R., Cross, L.E. and Goswami, A.K. (1966). Phenomenological Theory of High Permittivity in Fine-Grained Barium Titanate. *Journal of the American Ceramic Society* 49: 33
- Capsoni, D., Bini, M., Massarotti, V., Chiodelli, G., Mozzatic, M.C. and Azzoni, C.B. (2004). Role of doping and CuO segregation in improving the giant permittivity of $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$. *Journal of Solid State Chemistry* 177: 4494
- Carter, C.B. and Norton, M.G. (2007). *Ceramic Materials Science and Engineering*. Springer Science & Business Media.
- Chenari, H.M., Hassanzadeh, A., Golzan, M.M., Sedghi, H. and Talebian, M. (2011). Frequency dependence of ultrahigh dielectric constant of novel synthesized SnO_2 nanoparticles thick films. *Current Applied Physics*, 11: 409-413
- Chin, Z.H. and Perng, T.P., (1997). Amorphization of Ni-Si-C ternary alloy powder by mechanical alloying. *Materials Science Forum* 235-238: 121-126.
- Choudhar, R.N.P. and Bhunia, U. (2002). Structural, Dielectric and Electrical Properties of $\text{ACu}_3\text{Ti}_4\text{O}_{12}$ (A=Ca, Sr and Ba). *Journal of Material Science*, 37 (24): 5177

- Chung, S.Y., Kim, I.D. and Kang, S.J.L. (2004). Strong nonlinear current-voltage behaviour in perovskite-derivative calcium copper titanate. *Nature Materials*, 3:774.
- Cinθο, O.M., Favilla, E.A.P. and Capocchi, J.D.T. (2007). Mechanical-thermal synthesis of chromium carbides. *Journal of Alloys and Compounds*, 439:189–195.
- Cook, B.A., Beaudry, B.J., Harringa, J.L. and Barnett, W.J. (1989). The preparation of Si-Ge thermoelectric materials by mechanical alloying. In *Proceedings of Intersociety Energy Conversion Engineering Conference*. IEEE, New York.
- Davies, D.K.(1972).Carrier transport in polythene. *Journal of Physics D: Applied Physics*, 5(1): 162.
- Dielectric Material Market by Technology (OLED, LED, TFT-LCD, LED-LCD, Plasma, LCOS, DLP), Application (Conventional, 3D, Transparent, Flexible), Material (Metal Oxide, a-Silicon, LTPS, PET, PEN, Photonic Crystals) & by Geography - Global Forecast to 2013 – 2020. March 2014 Retrieved from <https://www.marketsandmarkets.com/>
- Espinoza, G.R., Vega, E., Tamayo, R., Criado, J.M. and Diáñez, M.J. (2014). Mechanochemical Processing of $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$ with Giant Dielectric Properties. *Materials and Manufacturing Processes*, 29(10): 1179-1183.
- Feng, T.T. and Shiau, H.K. (2004). Mechanism for Developing the Boundary Barrier Layers of $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$. *Journal of the American Ceramic Society*, 87:2072
- Fleury, P.A., Scott, J.F. and Worlock, J.M. (1968) Soft Phonon Modes and the 110K Phase Transition in SrTiO_3 . *Physical Review Letters* 21: 16
- Frederikse, H.P.R., Thurber, W.R. and Hosler, W.R. (1964). Electronic Transport in Strontium Titanate. *Physical Review* 134: A442
- Fritsch, S.G., Lebey, T., Boulos, M. and Durand, B. (2006). Dielectric properties of $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$ based multiphased ceramics. *Journal of the European Ceramic Society*, 26: 1245
- Gheisari, K.H., Javadpour, S., Oh, J.T. and Ghaffari, M. (2009). The effect of milling speed on the structural properties of mechanically alloyed Fe–45%Ni powders. *Journal of Alloys and Compounds* 472: 416–420
- Haeni, J.H., Irvin, P., Chang, W., Uecker, R., Reiche, P., Li, Y.L. et al. (2004). Room-temperature ferroelectricity in strained SrTiO_3 . *Nature*, 430:758-761
- Higuchi, T., Tsukamoto, T., Sata, N., Ishigame, M., Tezuka, Y. and Shin, S. (1998). Electronic structure of p-type SrTiO_3 by photoemission spectroscopy. *Physical Review B*, 57:6978
- Hippel, V.A., Breckenridge, R.C., Chesley, F.G. and Tisza, L. (1946). High dielectric constant ceramics. *Industrial and Engineering Chemistry* 38:1097
- Homes, C.C., Vogt, T., Shapiro, S.M., Wakimoto, S. and Ramirez, A.P. (2001). *Science*, 293: 673-676.
- Huang, H. and McCormick, P.G. (1997). Effect of milling conditions on the synthesis of chromium carbides by mechanical alloying. *Journal of Alloys and Compounds*, 256 1-2: 258-262.

- Jantunen, H. (2001). *A Novel Low Temperature Cofire Ceramic (LTCC) Material for Telecommunication Devices*. Thesis Department of Electrical Engineering Oulu University
- Jonscher, K. (1983). *Dielectric relaxation in solids*. Chelsea Dielectric Press.
- Kai, C., Wei, L., Fei, L.Y., Peng, B., Mei, L.X. and Song, Z.J. (2004). Investigation of the Size Effect on the Giant Dielectric Constant of $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$. *Chinese Physics Letters* 21: 1815
- Kang, S.J.L. (2005). Sintering Densification, grain growth & microstructure. Elsevier, Amsterdam.
- Kao, K.C. (2004). *Dielectric Phenomena in Solids*. Elsevier.
- Kinoshita, K. and Yamaji, A. (1976). Grain-size effects on dielectric properties in barium titanate ceramics. *Journal of Applied Physics*, 47: 371.
- Kniekamp, H. and Heywang, W. (1954). Depolarisationseffekte in polykristallin gesintertem BaTiO_3 . *Z. Angew. Phys.* 6:385.
- Kolodiaznyi, T. and Petric, A. (2005). The Applicability of Sr-deficient *n*-type SrTiO_3 for SOFC Anodes. *Journal of Electroceramics*, 15(1): 5-11
- Koonce, C.S., Cohen, M.L., Schooley, J.F., Hosler, W.R. and Pfeiffer, E.R. (1967). Superconducting Transition Temperatures of Semiconducting SrTiO_3 . *Physical Review*, 163: 380
- Krueger, D.S. and Lombardo, S.J. (2007). The effect of processing conditions and porosity on the electrical properties of Y_2O_3 -doped SrTiO_3 internal boundary layer capacitors. *Journal of Ceramic Processing Research* 8: 31–37.
- Kumar, G. B. and Buddhudu, S. (2010). Optical, thermal and dielectric properties of $\text{Bi}_4(\text{TiO}_4)$ ceramic powders. *Ceramics International*, 36:1857-1861.
- Kurtz, S.R., Arnold, C.J. and Hughes, R.C. (1983). Effect of chemical doping on the radiation-induced conductivity of polyethylene terephthalate. *Applied Physics Letters*, 43:1132
- Leapman, R.D., Grunes, L.A. and Fejes, P.L. (1982). Study of the L_{23} edges in the 3d transition metals and their oxides by electron-energy-loss spectroscopy with comparisons to theory. *Physical Review B*, 26: 614.
- Lü, L. and Lai, M.O. (1998). Mechanical alloying. Springer Science & Business Media.
- Lytle, F.W. (1964). X-Ray Diffractometry of Low-Temperature Phase Transformations in Strontium Titanate. *Journal of Applied Physics* 35:2212
- Maex, K., Baklanov, M.R., Shamiryan, D., Iacopi, F., Brongersma, S.H. and Yanovit, S.Z.S. (2003). Low dielectric constant materials for microelectronics. *Journal of Applied Physics* 93: 8793-8841
- Mahato, D.K., Dutta, A. and Sinha, T.P. (2011). Dielectric relaxation in double perovskite oxide, $\text{Ho}_2\text{CdTiO}_6$. *Bulletin of Materials Science*, 34(3): 455–462.
- Manik, S. and Pradhan, S. (2006). Microstructure characterization of ball-mill-prepared nanocrystalline $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$ by rietveld method. *Physica E: Low-Dimensional Systems and Nanostructures*, 33(1): 160–168

- Melanie, S. (2014). *Microstructure Evolution in Strontium Titanate: Investigated by means of grain growth simulations and x-ray diffraction contrast tomography experiments*. Karlsruher Institut für Technologie (KIT).
- Mishra, S.R., Long, G.J., Grandjean, F., Hermann, R.P., Roy, S., Ali, N. and Viano, A.M. (2003). Magnetic Properties of Iron. Nitride-Alumina Nanocomposite Materials prepared by High-Energy Ball Milling. *The European Physical Journal D* 24: 93–96
- Mohamed, J.J., Hutagalung, S.D., Ain, M.F., Deraman, K. and Ahmad, Z.A. (2007). Microstructure and dielectric properties of $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$ ceramic. *Material Letter*, 61:p. 1835–1838.
- Müller, K.A. and Burkhard, H. (1979). SrTiO_3 : An intrinsic quantum paraelectric below 4 K. *Physical Review B* 19: 3593
- Pinheiro, A., Saraiva, G., Filho, J. and Sombra, A. (2013). Preparation of $\text{Bi}_4\text{Ti}_3\text{O}_{12}$ (BIT) Ceramics via a High-Energy Ball Milling Process Doped with Multi-Walled Carbon Nanotubes (MWNTs). *Materials Sciences and Applications* 4:549-555.
- Ponpandian, N., Balaya, P. and Narayanasamy, A. (2002). Electrical conductivity and dielectric behavior of nanocrystalline NiFe_2O_4 spinel. *Journal of Physics: Condensed Matter*, 14: 3221.
- Prasad, K.V.R., Raju, A.R. and Varma, K.B.R. (1994). Grain size effects on the dielectric properties of ferroelectric $\text{Bi}_2\text{VO}_{5.5}$ ceramics. *Journal of Material Science*, 29: 2691–2696
- Rahaman, M.N. (2003). *Ceramic Processing And Sintering*. CRC Press
- Rahmati, B.(2004). Microstructural Studies on the Reoxidation Behavior of Nb -doped SrTiO_3 Ceramics, PhD thesis. Max-Planck- Institut für Metallforschung Stuttgart.
- Ramirez, A.P., Subramanian, M.A., Gardel, M., Blumberg, G., Li, D., Vogt, T. and Shapiro, S.M. (2000). Giant dielectric constant response in a copper-titanate. *Solid State Communications*, 115; 217-220.
- Rao, C.N.R. and Thomas, J.M. (1985). Intergrowth structures: the chemistry of solid-solid interfaces. *Accounts of Chemical Research*, 18; 113-119.
- Reshak, A.H., Roknabadi, M.R., Masoud, M., Zaboli, M., Bedhani, M. (2014). Influence of Mechanical Alloying on Dielectric Features of Ferroelectric BaTiO_3 Microcrystals. *International Journal of Electrochemical Science*,9: 720-727.
- Rochman, N.T., Kawamoto, K., Sueyoshi, H., Nakamura, Y. and Nishida, T. (2003). Effect of milling speed on an Fe–C–Mn system alloy prepared by mechanical alloying. *Journal of Materials Processing Technology* 138: 41–46.
- Rodriguez, V.A.P., Marcatoma, J.Q., Andrade, J.M.A., Saitovitch, E.M.B., Villegas, A.C. and Passamani, E.C. (2006). Influence of milling container internal geometry on the mechanical alloying process of the $\text{Fe}_{75}\text{Si}_{15}\text{B}_{10}$ system. *Materials Science and Engineering A* 429: 261–265.
- Rukmini, H.R., Choudhary, R.N.P. and Prabhakara, D.L. (2000). Effect of sintering temperature on dielectric properties of $\text{Pb}_{0.91}(\text{La}_{1-z/3}\text{Li}_z)_{0.09}(\text{Zr}_{0.65}\text{Ti}_{0.35})_{0.9775}\text{O}_3$ ceramics. *Materials Letters* 44: 96–104

- Schmidt, R. et al. (2012). Effects of Sintering Temperature on the Internal Barrier Layer Capacitor (IBLC) Structure in $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$ (CCTO) Ceramics. *Journal of the European Ceramic Society*, 32: 3313
- Schooley, J.F., Hosler, W.R. and Cohen, M.L. (1964). Superconductivity in Semiconducting SrTiO_3 . *Physical Review Letters* 12: 474
- Shannon, R.D. (1993). Dielectric polarizabilities of ions in oxides and fluoride. *Journal of Applied Physics*, 73: 348–366.
- Shao, S.F., Zhang, J.L., Zheng, P. and Wang, C.L. (2007). Effect of Cu-stoichiometry on the dielectric and electric properties in $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$ ceramics. *Solid state Communication* 142: 281
- Shirane, G. and Yamada, Y. (1969). Lattice-Dynamical Study of the 110K Phase Transition in SrTiO_3 . *Physical Review* 177:858
- Singh, H., Kumar, A. and Yadav, K.L. (2011) Structural, Dielectric, Magnetic, Magnetodielectric and Impedance Spectroscopic Studies of Multiferroic BiFeO_3 - BaTiO_3 Ceramics. *Materials Science and Engineering: B*, 176: 540-547.
- Subramanian, M.A. and Sleight, A.W. (2002). $\text{ACu}_3\text{Ti}_4\text{O}_{12}$ and $\text{ACu}_3\text{Ru}_4\text{O}_{12}$ perovskites: high dielectric constants and valence degeneracy. *Solid State Sciences*, 4: 347.
- Subramanian, M.A., D. Li, N. Duan, B.A. Reisner, A. Sleight, (2000). High dielectric constant in $\text{ACaCu}_3\text{Ti}_4\text{O}_{12}$ and $\text{ACaCu}_3\text{Ti}_4\text{O}_{12}$ phases. *Journal of Solid State Chemistry*. 151(2):323–325
- Suryanarayana, C. (1995). Does a disordered γ -TiAl phase exist in mechanically alloyed Ti-Al powders?. *Intermetallics* 3:153-160.
- Suryanarayana, C. (2001). Mechanical alloying and milling. *Progress in Materials Science*, 46: 1-184.
- Suryanarayana, C. and Froes, F.H. (1992). The structure and mechanical properties of metallic nanocrystals. *Metallurgical Transactions A*, 23: 1071-1081.
- Tsangaris, G.M., Psarras, G.C. and Kouloumbi, N. (1998). Electric modulus and interfacial polarization in composite polymeric systems. *Journal of Material Science*, 33: 2027
- Uchino, K., Sadanaga, E. and Hirose, T. (1989). Dependence of the Crystal Structure on Particle Size in Barium Titanate. *Journal of the American Ceramic Society* 72: 1555
- Varga, K.M. and Beke, D.L. (1996). Phase Transition in Cu-Sb Systems Induced by Ball Milling. *Materials Science Forum* 225-227: 465-470.
- Wang, C.M. et al. (2010). Microstructural and electrical properties of CaTiO_3 – $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$ ceramics. *Journal of Alloys and Compounds*, 491:423–430
- Wong, Y.J., Jumiah, H., Hashim, M., Wong, S.Y. and Yan, L.C. (2012). Effect of Milling Time on Microstructure, Crystallite Size and Dielectric Properties of SrTiO_3 Ceramic Synthesized via Mechanical Alloying Method. *Advanced Materials Research* 364: 388-392
- Yamaji, A., Enomoto, E., Kinoshita, K. and Murakami, T. (1977). Preparation, Characterization, and Properties of Dy-Doped Small-Grained BaTiO_3 Ceramics. *Journal of the American Ceramic Society* 60:97
- Yan, L. C., et al. (2011). Effect of Sintering Temperatures on the Microstructure and Dielectric Properties of SrTiO_3 . *World Applied Sciences Journal*, 14 (7), 1091-1094.

- Yeoh, C.K., Ahmed, M.F. and Ahmed, Z.A. (2007). Effects of Cu and Ti excess on the dielectric properties of $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$ prepared using a wet chemical method. *Journal of Alloys and Compounds* 443, 155.
- Yuan, J.; Lin, Y.H.; Lu, H.; Cheng, B.; Nan, C.W.(2011). Dielectric and varistor behavior of $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$ - MgTiO_3 composite ceramics. *Journal of the American Ceramic Society*, 94, 1966–1969.
- Zheng, P., et al. (2012). Grain-size effects on dielectric and piezoelectric properties of poled BaTiO_3 ceramics. *Acta Materialia*, 60(13-14): 5022-5030.

